# UTC UNISONIC TECHNOLOGIES CO., LTD

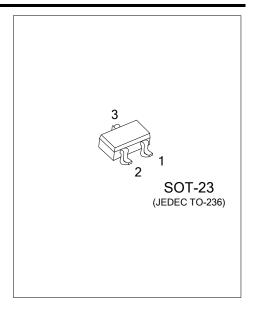
## **MMBT9014**

#### NPN SILICON TRANSISTOR

## PRE-AMPLIFIER, LOW LEVEL & LOW NOISE

#### **FEATURES**

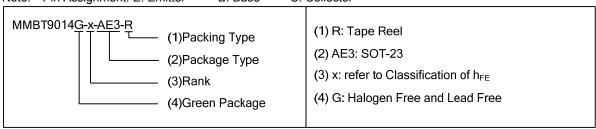
- \* High Total Power Dissipation. (450mW)
- \* Excellent hee Linearity.
- \* Complementary to UTC MMBT9015



#### ORDERING INFORMATION

Oudoving Number	Package	Pin Assignment			Doolsing	
Ordering Number		1	2	3	Packing	
MMBT9014G-x-AE3-R	SOT-23	E	В	С	Tape Reel	

Note: Pin Assignment: E: Emitter B: Base C: Collector



#### **MARKING**



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#### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage	$V_{\sf CEO}$	45	V
Collector-Base Voltage	$V_{CBO}$	50	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	Ic	100	mA
Collector dissipation	Pc	225	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

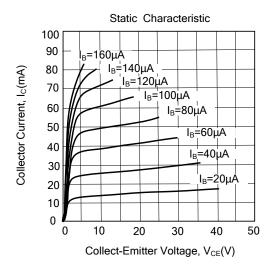
#### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

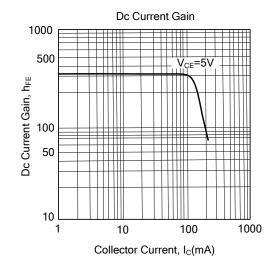
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Voltage	$V_{CEO}$	I <sub>C</sub> =100μA, I <sub>E</sub> =0	50			V
Collector-Base Voltage	$V_{CBO}$	I <sub>C</sub> =1mA, I <sub>B</sub> =0	45			V
Emitter Base Voltage	$V_{EBO}$	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cutoff current	I <sub>CBO</sub>	$V_{CB}$ =50V, $I_E$ =0			50	nA
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{EB}$ =5 $V$ , $I_{C}$ =0			100	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V,Ic=1mA	60	280	1000	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA		0.14	0.3	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA		0.84	1.0	V
Base-emitter on voltage	$V_{BE(ON)}$	V <sub>CE</sub> =5V, I <sub>C</sub> =2mA	0.58	0.63	0.7	V
Current-Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	150	270		MHz
Output Capacitance	Сов	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		2.2	3.5	pF
Noise Figure	NF	$V_{CE}$ =5 $V$ , $I_{C}$ =0.2 $m$ A, $f$ =1 $K$ Hz, $R_{S}$ =2 $K$ $\Omega$		0.9	10	dB

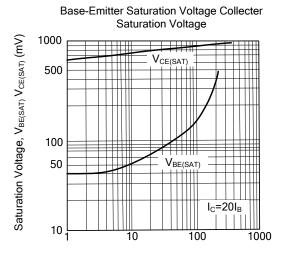
#### ■ CLASSIFICATION OF h<sub>FE</sub>

RANK	А	В	С	D
RANGE	60-150	100-300	200-600	400-1000

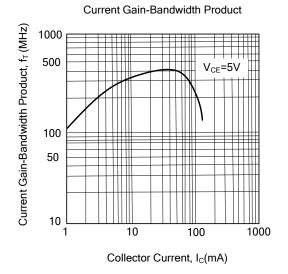
#### TYPICAL CHARACTERISTICS







Collector Current, I<sub>C</sub>(mA)



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